

Standard Rectifier Module

1~ Rectifier	
V_{RRM}	= 1200 V
I_{DAV}	= 60 A
I_{FSM}	= 550 A

1~ Rectifier Bridge

Part number

VBO52-12NO7



 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

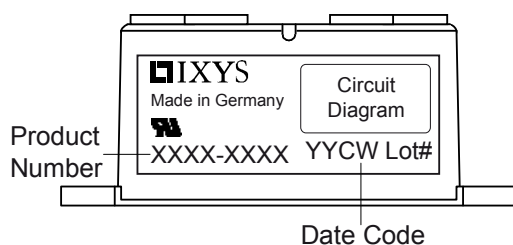
- Diode for main rectification
- For one phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-D

- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_R	reverse current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			40	μA
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			1.5	mA
V_F	forward voltage drop	$I_F = 20\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.07	V
		$I_F = 40\text{ A}$				1.19	V
		$I_F = 20\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			0.96	V
		$I_F = 40\text{ A}$				1.13	V
I_{DAV}	bridge output current	$T_C = 115^{\circ}\text{C}$	$T_{VJ} = 150^{\circ}\text{C}$			60	A
		rectangular $d = 0.5$					
V_{FO}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.78	V
r_F	slope resistance					8.1	m Ω
R_{thJC}	thermal resistance junction to case					1.1	K/W
R_{thCH}	thermal resistance case to heatsink				0.4		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				110	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}\text{C}$			550	A
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			595	A
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}\text{C}$			470	A
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			505	A
I^2t	value for fusing	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}\text{C}$			1.52	kA ² s
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			1.48	kA ² s
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}\text{C}$			1.11	kA ² s
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			1.06	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V; } f = 1\text{ MHz}$		$T_{VJ} = 25^{\circ}\text{C}$		19	pF

Package PWS-D			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			150	A
T_{stg}	storage temperature		-40		125	°C
T_{VJ}	virtual junction temperature		-40		150	°C
Weight				153		g
M_D	mounting torque		4.25		5.75	Nm
M_T	terminal torque		4.25		5.75	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	9.5			mm
$d_{Spb/Apb}$		terminal to backside	26.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VBO52-12NO7	VBO52-12NO7	Box	10	472344

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^\circ\text{C}$

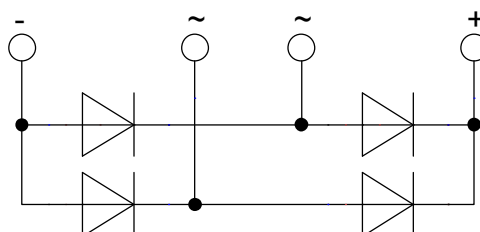
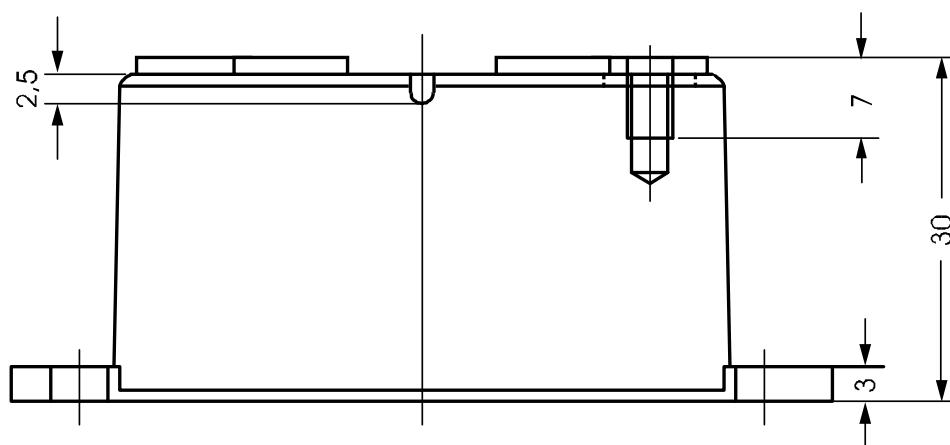


Rectifier

$V_{0\max}$	threshold voltage	0.78	V
$R_{0\max}$	slope resistance *	6.9	mΩ

Technical drawing of a rectangular plate with the following dimensions and features:

- Overall width: 72
- Overall height: 42
- Top edge features:
 - Left corner: 21,6
 - Left side: 5,3
 - Right side: 5,3
 - Right corner: 13,3
- Internal dimensions:
 - Top section: 20, 2,5, 18, 2,5, 20
 - Bottom section: 23, 10, 48
- Features:
 - Top section: Three rectangular slots, each containing a hexagonal hole. The middle slot is labeled with a tilde (~).
 - Bottom section: Two rectangular slots, each containing a circular hole. The left slot is labeled with a plus (+) and the right slot with a minus (-).
 - Left side: A circular hole.
 - Right side: A circular hole.
- Material: M5



Rectifier

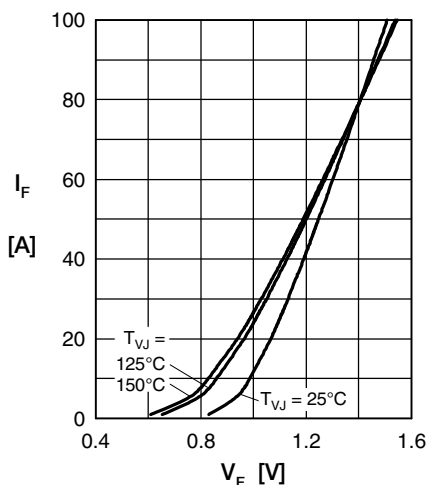


Fig. 1 Forward current vs. voltage drop per diode

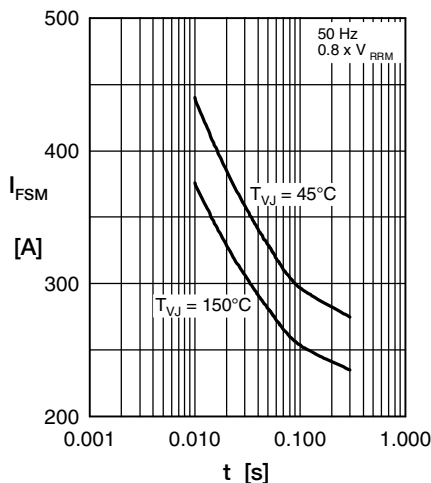


Fig. 2 Surge overload current vs. time per diode

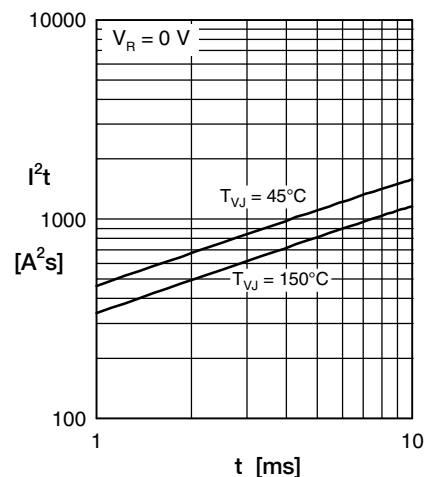


Fig. 3 I^2t vs. time per diode

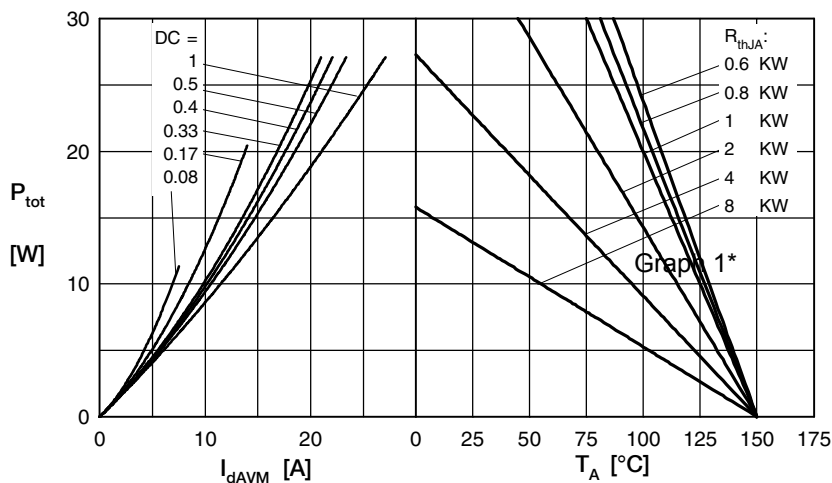


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

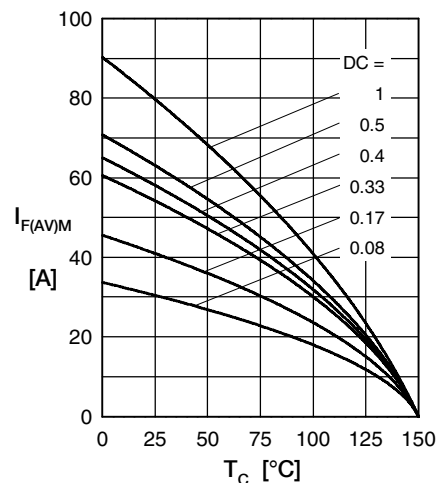


Fig. 5 Max. forward current vs. case temperature per diode

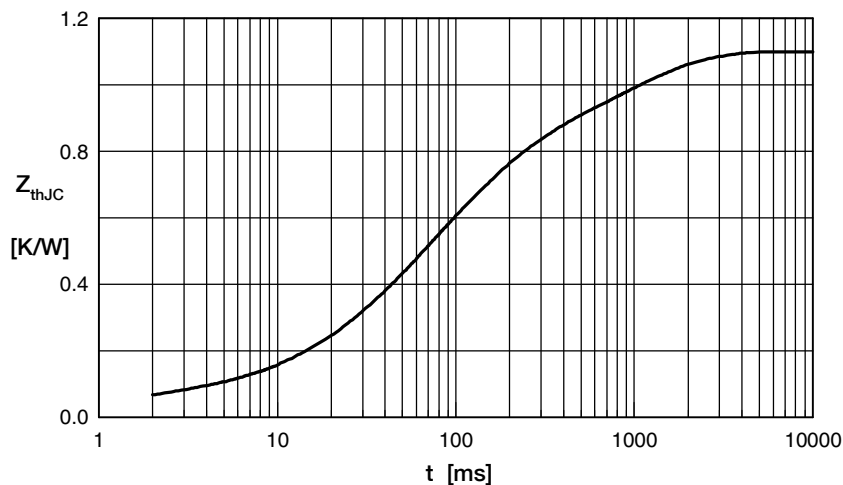


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.05	0.001
2	0.14	0.030
3	0.25	0.060
4	0.35	0.130
5	0.31	0.920